

4V Drive Pch MOSFET

RP1E050RP

Structure

Silicon P-channel MOSFET

● Features

- 1) Low On-resistance.
- 2) High power package.
- 3) 4V drive.

Application

Switching

Packaging specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	1000	
RP1E050R	0		

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	-30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_{D}	±5	Α
	Pulsed	I _{DP} *1	±20	Α
Source current (Body Diode)	Continuous	I _S	-1.6	Α
	Pulsed	I _{SP} *1	-20	Α
Power dissipation		P _D *2	2.0	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

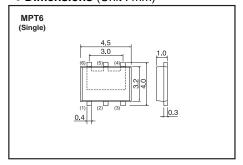
^{*1} Pw≤10µs, Duty cycle≤1%

• Thermal resistance

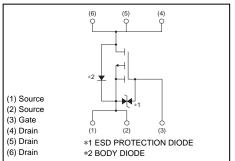
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	62.5	°C/W

^{*}Mounted on a ceramic board.

Dimensions (Unit : mm)



• Inner circuit



^{*2} Mounted on a ceramic board.

● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	1	-	±10	μA	$V_{GS}=\pm20V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	I _D =-1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	1	-	-1	μA	V_{DS} =-30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	-	-2.5	V	V_{DS} =-10V, I_{D} =-1mA
Otatia duain accura an atata		1	36	50		$I_D = -5A, V_{GS} = -10V$
Static drain-source on-state resistance	R _{DS (on)} *	1	52	72	mΩ	$I_D = -2.5A, V_{GS} = -4.5V$
Toolotarioo		-	58	80		I _D =-2.5A, V _{GS} =-4.0V
Forward transistor admittance	I Y _{fs} ľ	4	-	-	S	$I_{D} = -5A, V_{DS} = -10V$
Input capacitance	C _{iss}	1	850	-	pF	V _{DS} =-10V
Output capacitance	C _{oss}	1	120	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	1	120	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	9	-	ns	I _D =−2.5A, V _D 5, −15V
Rise time	t _r *	1	25	-	ns	V _{GS} =-10V
Turn-off delay time	t _{d(off)} *	1	55	-	ns	$R_L=6.0\Omega$
Fall time	t _f *	-	30	-	ns	$R_G=10\Omega$
Total gate charge	Q _g *	-	9.2	-	nC	I _D =-5A, V _{DD} ≒-15V
Gate-source charge	Q _{gs} *	-	2.4	-	nC	V_{GS} =-5V R_L =3.0 Ω
Gate-drain charge	Q _{gd} *	-	3.6	-	nC	$R_G=10\Omega$

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	-1.2	V	$I_s=-5A$, $V_{GS}=0V$

^{*}Pulsed

• Electrical characteristics curves

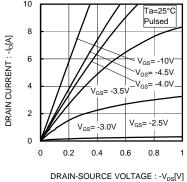
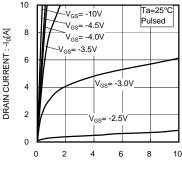
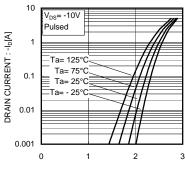


Fig.1 Typical Output Characteristics(I)



DRAIN-SOURCE VOLTAGE: -VDS[V]

Fig.2 Typical Output Characteristics(${\mathbb I}$)



GATE-SOURCE VOLTAGE : -V_{GS}[V]

Fig.3 Typical Transfer Characteristics

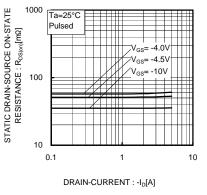
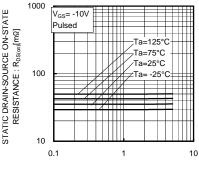


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)



DRAIN-CURRENT : -I_D[A]

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

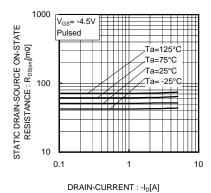


Fig.6 Static Drain-Source On-State

Resistance vs. Drain Current(Ⅲ)

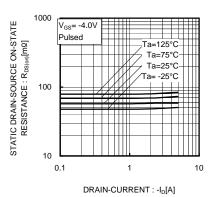
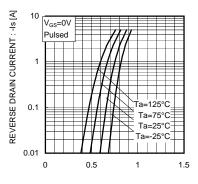


Fig.7 Static Drain-Source On-State

Resistance vs. Drain Current(IV)

FORWARD TRANSFER ADMITTANCE: |Yfs| [S] 10 V_{DS}= -10V Pulsed Ta= -25°C Ta=25°C Ta=75°C Ta=125°C 0.01 0.1 10 DRAIN-CURRENT : -I_D[A]

Fig.8 Forward Transfer Admittance vs. Drain Current



SOURCE-DRAIN VOLTAGE : $-V_{SD}[V]$ Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

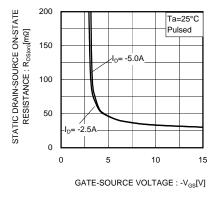


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

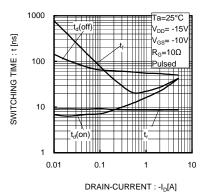
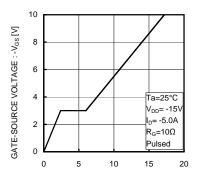
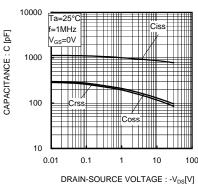


Fig.11 Switching Characteristics



TOTAL GATE CHARGE : Qg [nC]
Fig.12 Dynamic Input Characteristics



RAIN-SOURCE VOLTAGE: -V_{DS}[V Fig.13 Typical Capacitance vs. Drain-Source Voltage

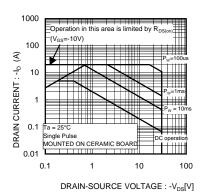


Fig.14 Maximum Safe Operating Area

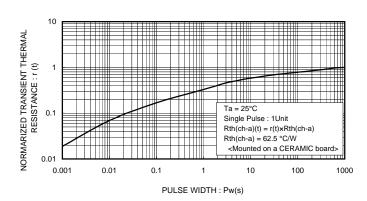


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

Measurement circuits

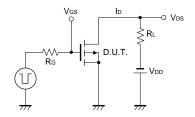


Fig.1-1 Switching Time Measurement Circuit

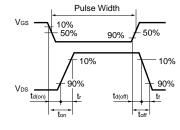


Fig.1-2 Switching Waveforms

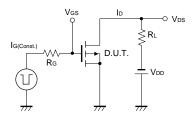


Fig.2-1 Gate Charge Measurement Circuit

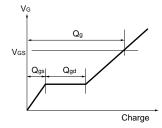


Fig.2-2 Gate Charge Waveform

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